AMENDMENTS TO THE CLAIMS

1. (Original) A structure comprising:

a substrate having a thickness defined by a first surface and a generally opposing second surface;

a trench having a long axis and received in the first surface and extending through less than an entirety of the thickness of the substrate; and,

a plurality of slots extending into the substrate from the second surface and connecting with the trench to form a compound slot through the substrate,

wherein a cross-section of the trench taken transverse the long axis has a first width that is proximate the first surface that is greater than a second width that is more distal to the first surface.

2. (Original) The structure of claim 1, wherein the substrate comprises silicon.

3. (Original) The structure of claim 1, wherein the substrate comprises a semiconductor substrate incorporated into a print cartridge.

4. (Original) The structure of claim 1, wherein the compound slot comprises a fluid-feed slot.

5. (Currently Amended) A structure comprising:

a substrate having a thickness defined by a first surface and a generally opposing second surface;

a trench having a long axis and received in the first surface and extending through less than an entirety of the thickness of the substrate; and,

a plurality of slots extending into the substrate from the second surface and connecting with the trench to form a compound slot through the substrate, wherein a cross-section of the trench taken transverse the long axis has a first width that is proximate the first surface that is less than a second width that is more distal to the first surface, and the plurality of slots are separated from each other via substrate material extending from the second surface.

6. (Original) The structure of claim 1, wherein the first width comprises a minimum width of the compound slot.

7. (Original) The structure of claim 1, wherein a maximum width of the compound slot is at the second surface.

8. (Withdrawn) A structure comprising: a substrate having a slot formed between a first surface and a generally opposing second surface, the slot extending along a long axis and being defined at least in part by at least one reinforcement structure which extends across the slot generally orthogonally to the long axis and wherein the reinforcement structure is defined, at least in part, by a portion proximate the first surface which approximates a portion of a triangle.

9. (Currently Amended) A structure comprising:

a substrate having a thickness and a first surface;

a trench having a first dimension and a second dimension with respect in the first surface, the trench extending through less than an entirety of the thickness of the substrate; and,

a plurality of slots extending into the substrate from a second surface and connecting with the trench to form a compound slot through the substrate, wherein the first dimension of the trench is greater than the second dimension, and the plurality of slots are separated from each other via substrate material extending from the second surface.

10. (Previously Presented) The structure of claim 9, wherein the substrate comprises silicon.

11. (Previously Presented) The structure of claim 9, further comprising a plurality of chambers that are in fluidic communication with the compound slot.

12. (Previously Presented) The structure of claim 10, further comprising a plurality of resistors that are configured to cause fluid to be ejected from the plurality of chambers.

13. (Previously Presented) The structure of claim 10, further comprising a plurality of fluid ejection elements each associated with one of the plurality of chambers.

14. (Previously Presented) The structure of claim 9, wherein the compound slot comprises a fluid-feed slot.

15. (Previously Presented) The structure of claim 9, wherein the first dimension is about 30 microns to about 300 microns.

16. (Previously Presented) The structure of claim 9, wherein the first dimension is about 200 microns.

17. (Previously Presented) The structure of claim 1, wherein the first dimension comprises a first width of about 30 microns to about 300 microns.

18. (Previously Presented) The structure of claim 17, wherein the first width is about 200 microns.